

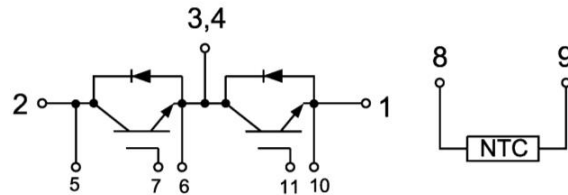


# GT300HF120T9H

## IGBT Module

### Features:

- Trench & Field Stop IGBT
- Short Circuit Rated >10 $\mu$ s
- Low Switching Loss
- 100% RBSOA Tested(2xIc)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



### Applications:

- Hybrid Electrical Vehicles(H)EV
- Automotive Applications
- Commercial Agriculture Vehicles
- Motor Drives

### IGBT, Inverter Maximum Rated Values

V <sub>CES</sub>	Collector-Emitter Blocking Voltage	T <sub>J</sub> =25°C	1200	V
V <sub>GES</sub>	Gate-Emitter Voltage		±20	V
I <sub>C</sub>	Continuous Collector Current	T <sub>C</sub> =100°C	300	A
		T <sub>C</sub> =25°C	580	A
I <sub>CM</sub>	Peak Collector Current Repetitive	tp=1ms	600	A
t <sub>sc</sub>	Short Circuit Withstand Time		>10	$\mu$ s
P <sub>D</sub>	Maximum Power Dissipation (IGBT)	T <sub>C</sub> =25°C T <sub>Jmax</sub> =175°C	1975	W



## Electrical Characteristics of IGBT

### Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=4mA, V_{CE}=V_{GE}, T_J=25^\circ C$	5.0	5.6	6.6	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=300A, V_{GE}=15V$	$T_J=25^\circ C$	1.70	1.90	V
			$T_J=125^\circ C$	1.90		V
			$T_J=150^\circ C$	2.00		V
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE}=0V, V_{CE}=V_{CES}, T_J=25^\circ C$			1	mA
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE}=\pm 20V, V_{CE}=0V, T_J=25^\circ C$			400	nA
$C_{ies}$	Input Capacitance	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_J=25^\circ C$		19.71		nF
$C_{oes}$	Output Capacitance			1.68		nF
$C_{res}$	Reverse Transfer Capacitance			1.10		nF

### Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600V, I_C=300A, R_{Gon}=2\Omega, V_{GE}=\pm 15V, \text{Inductive Load}$	$T_J=25^\circ C$	0.39		$\mu s$
			$T_J=125^\circ C$	0.40		
			$T_J=150^\circ C$	0.40		
$t_r$	Rise Time		$T_J=25^\circ C$	0.13		$\mu s$
			$T_J=125^\circ C$	0.13		
			$T_J=150^\circ C$	0.13		
$t_{d(off)}$	Turn-off Delay Time		$T_J=25^\circ C$	0.39		$\mu s$
			$T_J=125^\circ C$	0.42		
			$T_J=150^\circ C$	0.42		
$t_f$	Fall Time	$T_J=25^\circ C$	0.13		$\mu s$	
		$T_J=125^\circ C$	0.19			
		$T_J=150^\circ C$	0.21			
$E_{on}$	Turn-on Switching Loss	$V_{CC}=600V, I_C=300A, R_{Gon}=2\Omega, V_{GE}=\pm 15V, di/dt=1880A/\mu s (T_J=150^\circ C) \text{ Inductive Load}$	$T_J=25^\circ C$	20.6		mJ
			$T_J=125^\circ C$	27.3		
			$T_J=150^\circ C$	29.7		



E <sub>off</sub>	Turn-off Switching Loss	V <sub>CC</sub> = 600V, I <sub>C</sub> =300A, R <sub>Goff</sub> = 2Ω, V <sub>GE</sub> = ±15V, du/dt=3300V/μs ( T <sub>J</sub> =150°C) Inductive Load	T <sub>J</sub> =25°C	26.7	mJ
			T <sub>J</sub> =125°C	35.6	
			T <sub>J</sub> =150°C	38.3	
Q <sub>g</sub>	Total Gate Charge	V <sub>GE</sub> =+15V...-15V	T <sub>J</sub> =25°C	1.56	μC
R <sub>g internal</sub>	Internal Gate Resistance		T <sub>J</sub> =25°C	2.5	Ω
RBSOA	I <sub>C</sub> =600A, V <sub>CC</sub> =1050V, V <sub>p</sub> =1200V, R <sub>Goff</sub> = 2Ω, V <sub>GE</sub> =+15V to 0V, T <sub>J</sub> =150°C		Trapezoid		
I <sub>SC</sub>	SC Data	V <sub>CC</sub> =600V, V <sub>GE</sub> =±15V, R <sub>Gon</sub> =2ohm, R <sub>Goff</sub> =2ohm, tp=10us, T <sub>J</sub> =125°C, Inductive Load		1594	A
R <sub>θJC</sub>	IGBT Thermal Resistance: Junction-To-Case(per leg)			0.076	°C/W

### Maximum Rated Values of Diode

V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	T <sub>J</sub> =25°C	1200	V
I <sub>F</sub>	Diode Continuous Forward Current		300	A
I <sub>FM</sub>	Diode Maximum Forward Current	tp=1ms	600	A
I <sup>2</sup> t	I <sup>2</sup> t - Value	V <sub>R</sub> =0V, t <sub>p</sub> =10ms, T <sub>J</sub> =125°C	19600	A <sup>2</sup> s
		V <sub>R</sub> =0V, t <sub>p</sub> =10ms, T <sub>J</sub> =150°C	15980	A <sup>2</sup> s

### Electrical Characteristics of Diode (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
V <sub>FM</sub>	Forward Voltage	I <sub>F</sub> =300A	T <sub>J</sub> =25°C	1.80		V
			T <sub>J</sub> =125°C	1.80		
			T <sub>J</sub> =150°C	1.80		
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =300A, -di <sub>F</sub> /dt =2010A/μs(T <sub>J</sub> =150°C), V <sub>R</sub> =600V, V <sub>GE</sub> = -15V	T <sub>J</sub> =25°C	0.41		μs
			T <sub>J</sub> =125°C	0.60		
			T <sub>J</sub> =150°C	0.64		
I <sub>rr</sub>	Peak Reverse Recovery Current	I <sub>F</sub> =300A, -di <sub>F</sub> /dt =2010A/μs(T <sub>J</sub> =150°C), V <sub>R</sub> =600V, V <sub>GE</sub> = -15V	T <sub>J</sub> =25°C	150		A
			T <sub>J</sub> =125°C	181		
			T <sub>J</sub> =150°C	191		



Q <sub>rr</sub>	Reverse Recovery Charge	I <sub>F</sub> =300A, -diF/dt =2010/μs(T <sub>J</sub> =150°C), V <sub>R</sub> =600V, V <sub>GE</sub> = -15V	T <sub>J</sub> =25°C	29.7	μC
			T <sub>J</sub> =125°C	50.7	
			T <sub>J</sub> =150°C	57.8	
E <sub>rec</sub>	Reverse Recovery Energy		T <sub>J</sub> =25°C	12.9	mJ
			T <sub>J</sub> =125°C	22.0	
			T <sub>J</sub> =150°C	25.4	
R <sub>θJC</sub>	Diode Thermal Resistance: Junction-To-Case (per leg)			0.134	°C/W

## Internal NTC-Thermistor Characteristics

Symbol	Description	Min	Typ	Max	Unit
R <sub>25</sub>	T <sub>C</sub> =25°C		5		kΩ
ΔR/R	T <sub>C</sub> =100°C, R <sub>100</sub> =481Ω	-5		+5	%
P <sub>25</sub>	T <sub>C</sub> =25°C			10	mW
B <sub>25/50</sub>	R <sub>2</sub> =R <sub>25</sub> exp[B <sub>25/50</sub> (1/T <sub>2</sub> -1/(298.15K))]		3380		K
B <sub>25/80</sub>	R <sub>2</sub> =R <sub>25</sub> exp[B <sub>25/80</sub> (1/T <sub>2</sub> -1/(298.15K))]		3440		K

## Module

Symbol	Description		Min.	Typ.	Max.	Units
V <sub>iso</sub>	Isolation Voltage (All Terminals Shorted)	RMS, f=50Hz, 1minute	2500			V
L <sub>sCE</sub>	Stray Inductance Module			20		nH
T <sub>J</sub>	Maximum Junction Temperature				150	°C
T <sub>JOP</sub>	Maximum Operating Junction Temperature Range		-40		+150	°C
T <sub>stg</sub>	Storage Temperature		-40		+125	°C
CTI	Comparative Tracking Index		200			
R <sub>θCS</sub>	Case-to-Sink Thermally (Conductive Grease Applied)				0.02	°C/W
M	Terminals Connection Torque	Screw M6-Mounting according to valid application note	3.0		6.0	N·m
M	Mounting Torque for Module Mounting	Screw M5--Mounting according to valid application note	3.0		6.0	N·m
G	Weight			330		g



## Ordering Information Table

Device code	G	T	300	HF	120	T9	H
	①	②	③	④	⑤	⑥	⑦

- ① - IGBT Module
- ② - Field Stop Trench Gate IGBT
- ③ - Rated Current (300=300A)
- ④ - Circuit Configuration (HF=Half Bridge)
- ⑤ - Rated Voltage (120=1200V)
- ⑥ - Package Type
- ⑦ - Test Level (Pass the Important Reliability Test-Industrial Grade)

DATA SHEET

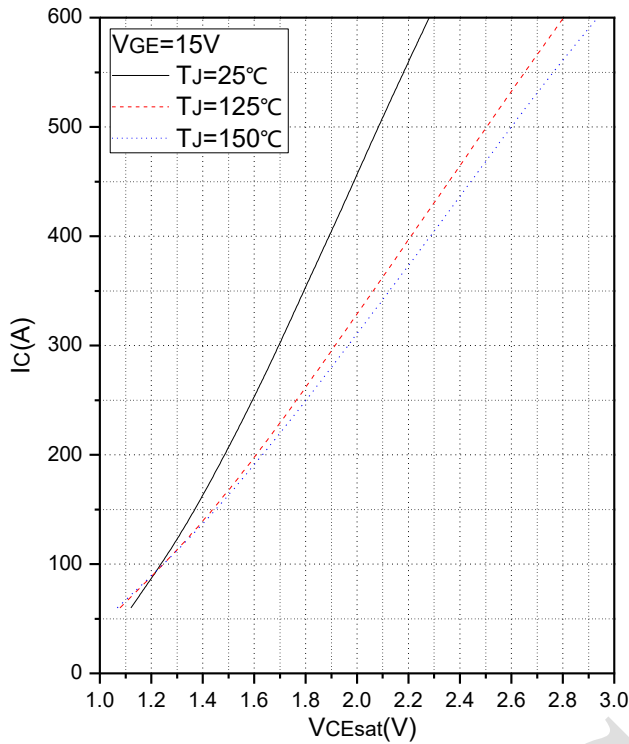


Fig.1 Typical Saturation Voltage Characteristics

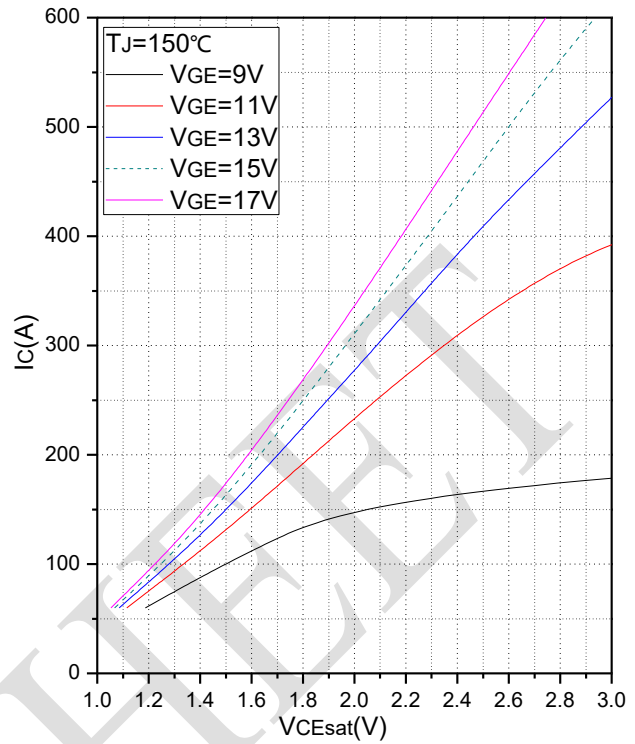


Fig.2 Typical Output Characteristics

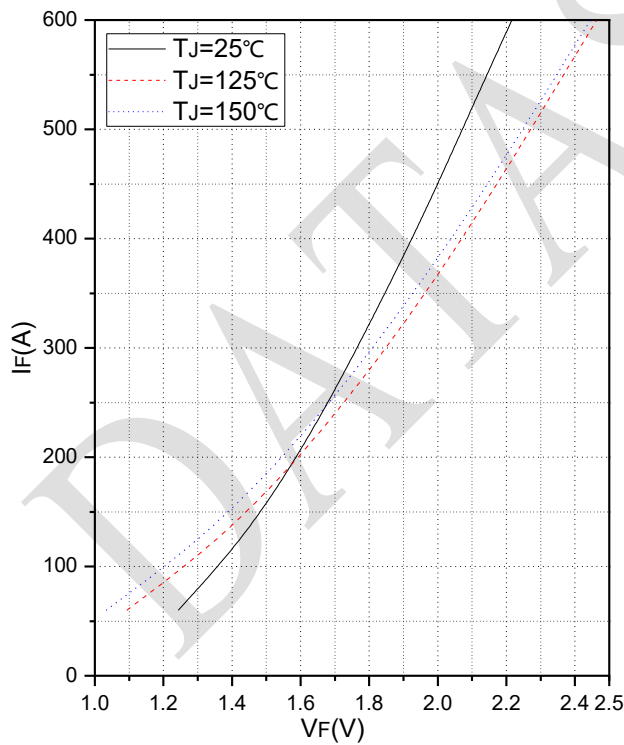


Fig.3 Forward Characteristics of Diode

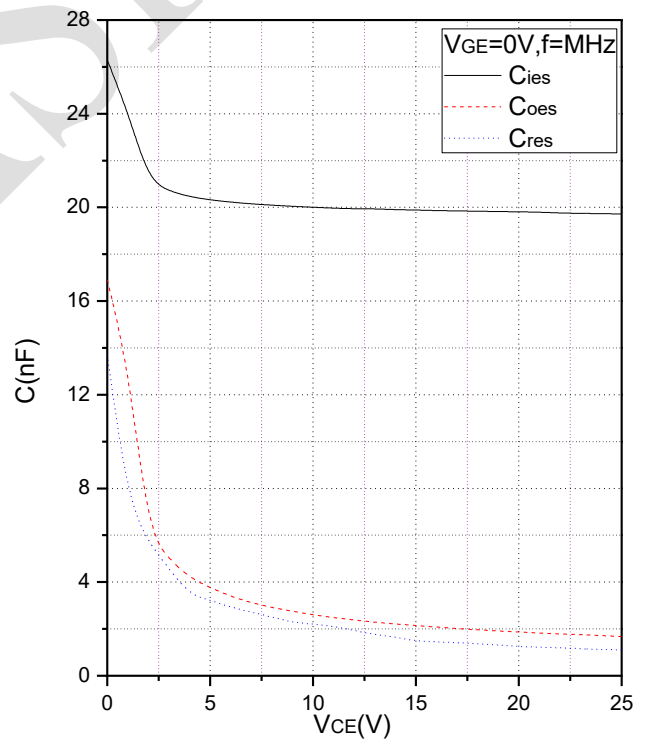


Fig.4 Capacitance Characteristics

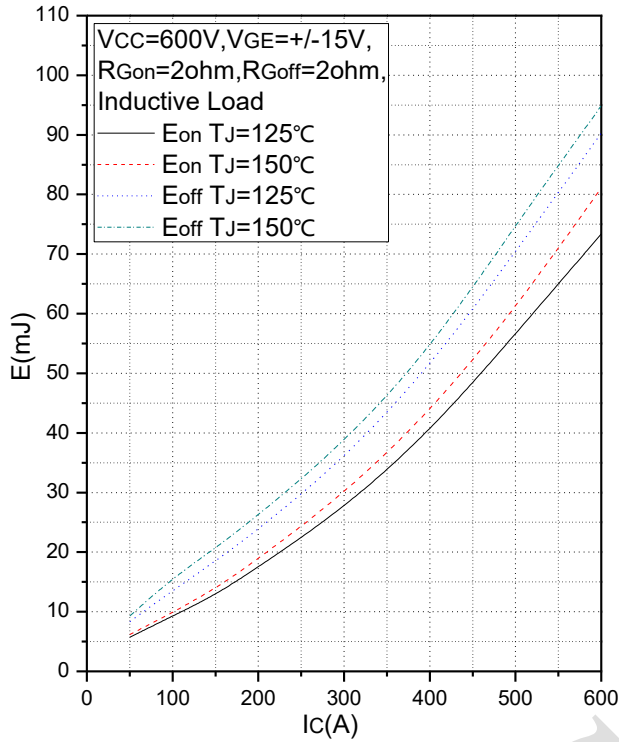


Fig.5 Typical Switching Loss vs. Collector Current

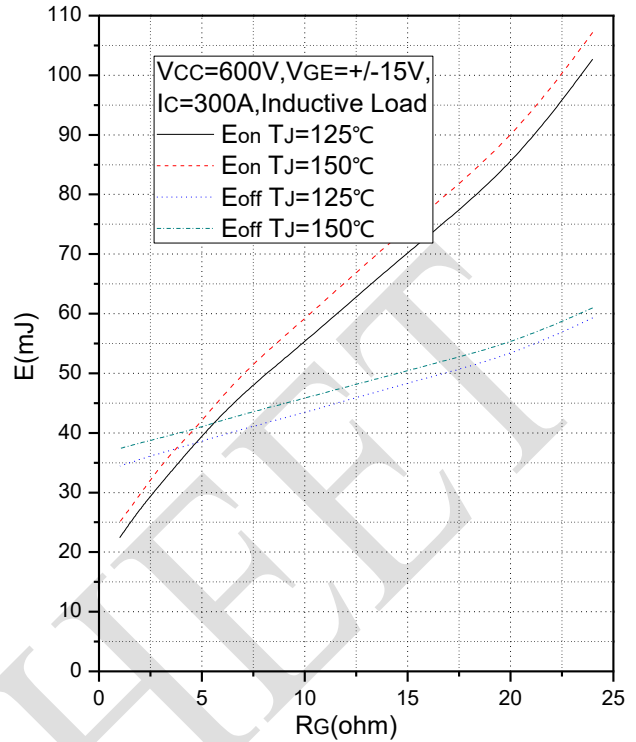


Fig.6 Typical Switching Loss vs. Gate Resistance

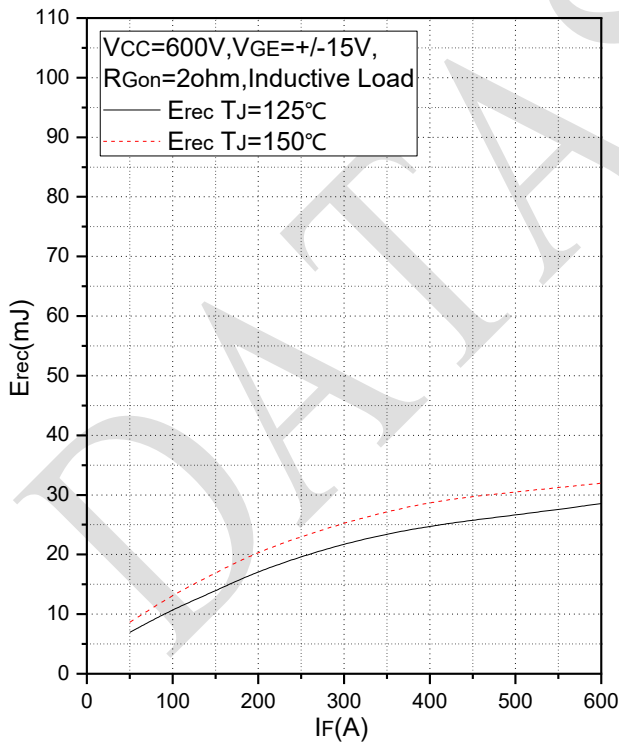


Fig.7 Typical Switching Loss vs. Forward Current

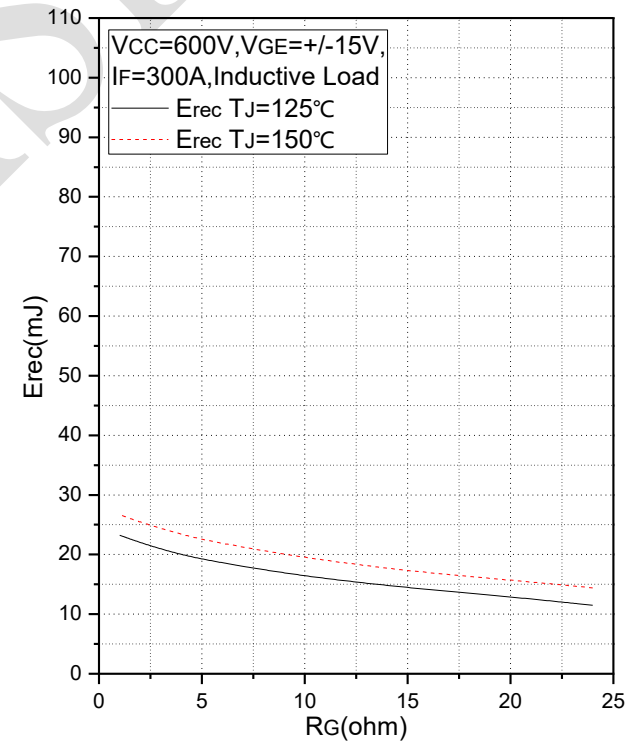


Fig.8 Typical Switching Loss vs. Gate Resistance

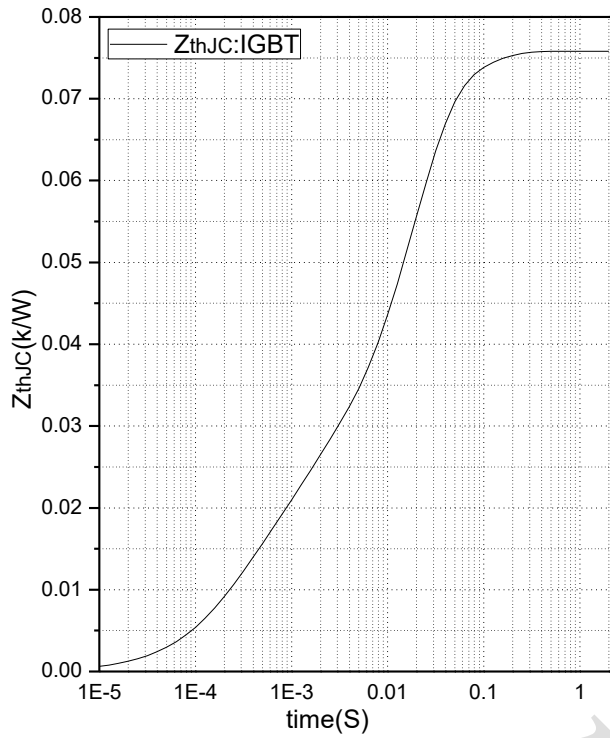


Fig.9 Transient Thermal Impedance (IGBT)

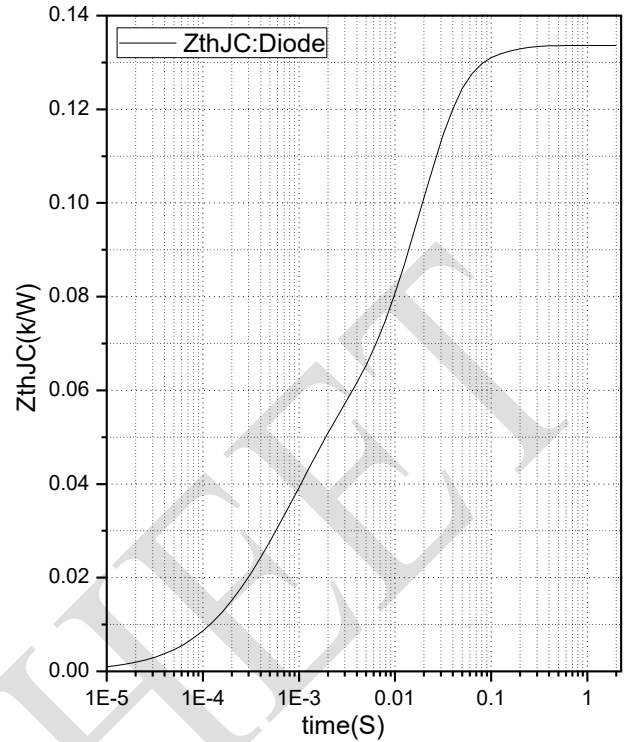


Fig.10 Transient Thermal Impedance (Diode)

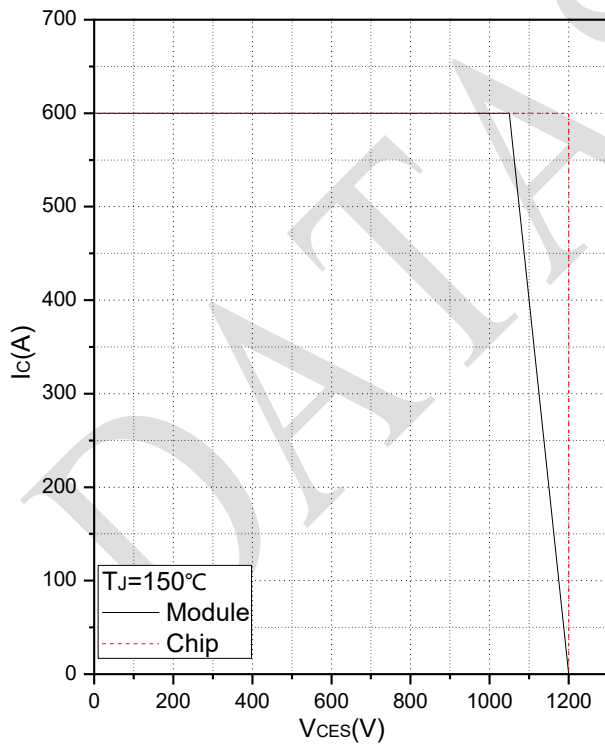


Fig.11 Reverse Bias Safe Operation Area (RBSOA)

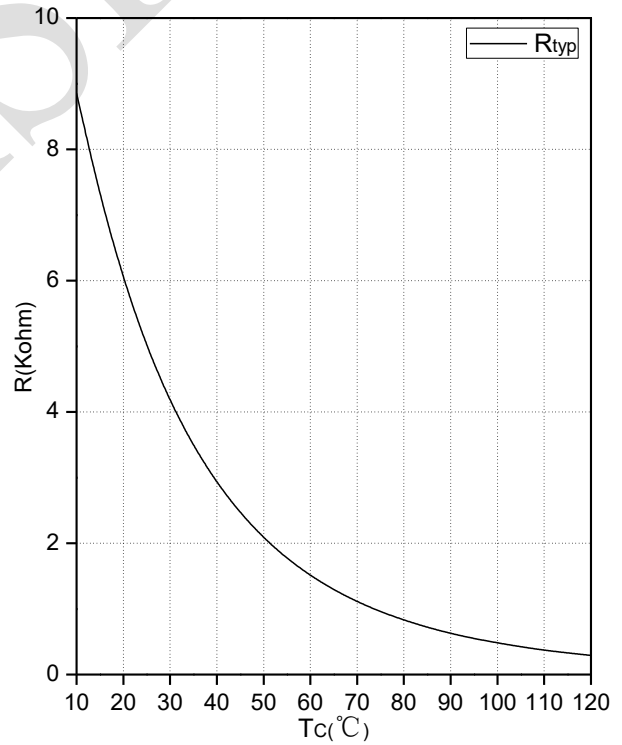
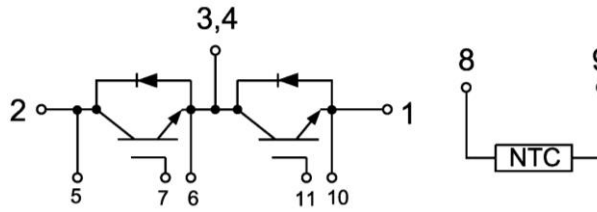


Fig.12 NTC Temperature Characteristics

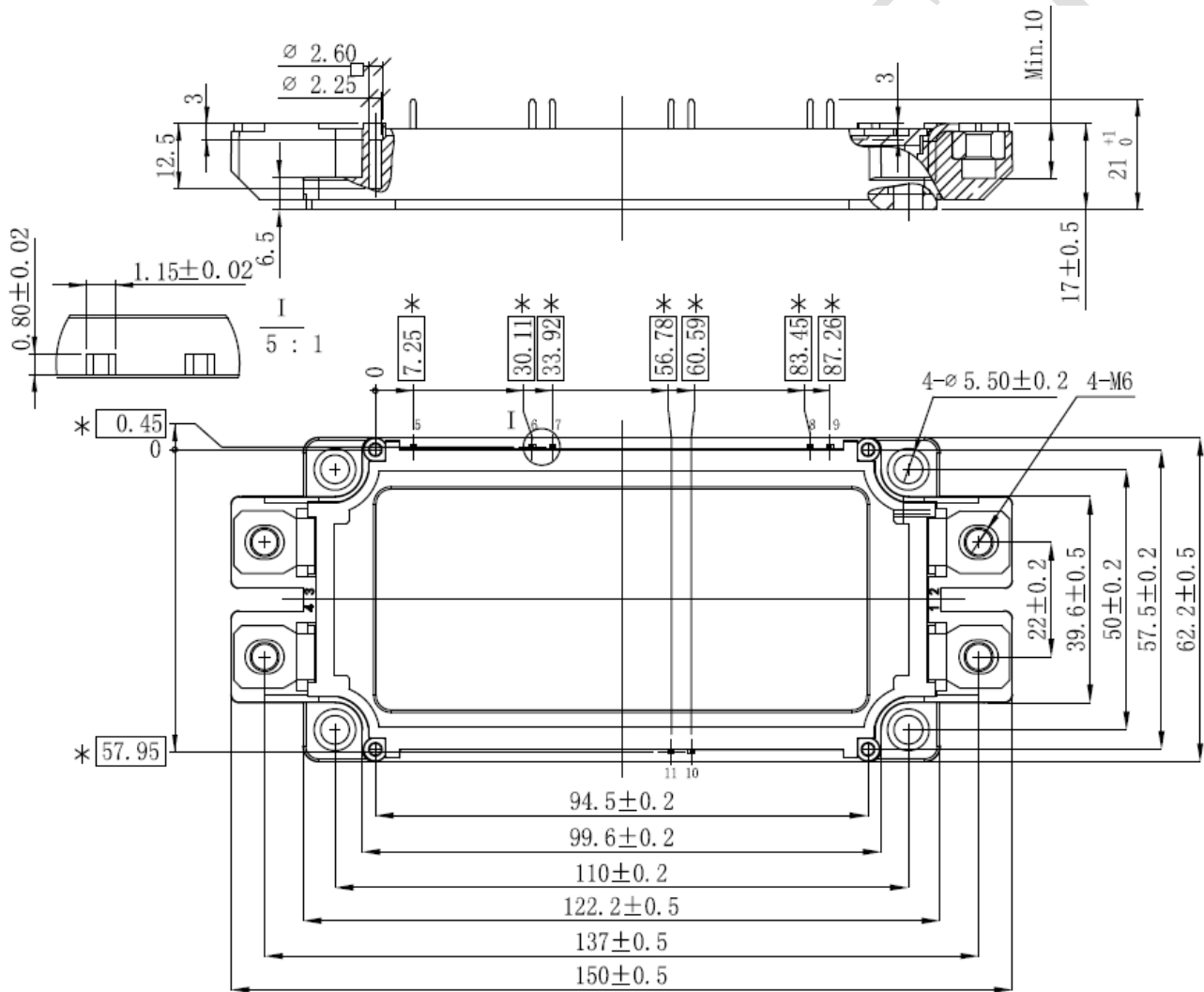




**Internal Circuit:**



**Package Outline (Unit: mm):**





Date	Revision	Notes
01/21/2019	01	Initial Release
08/11/2022	A	Final Version

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